

# isc N-Channel MOSFET Transistor

### IRFB3806, IIRFB3806

### FEATURES

- Static drain-source on-resistance: R<sub>DS</sub>(on) ≤15.8mΩ
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

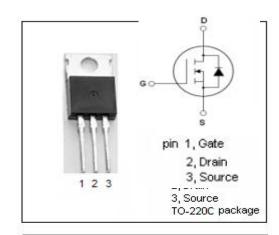
 Suitable for High speed power switching and high efficiency synchronous rectification in SMPS

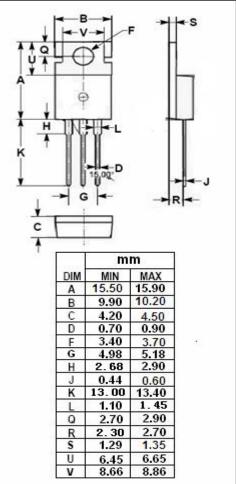
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	60	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Drain Current-Continuous	43	А	
I <sub>DM</sub>	Drain Current-Single Pulsed	170	Α	
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	71	W	
Tj	Max. Operating Junction Temperature	175	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature	-55~175	$^{\circ}$	

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	2.12	°C/W
Rth(ch-a)	Channel-to-ambient thermal resistance	62	°C/W







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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A	60			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID =50 μ A	2		4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =25A			15.8	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =60V; V <sub>GS</sub> = 0V			20	μА
V <sub>SD</sub>	Diode forward voltage	Is=25A, V <sub>GS</sub> = 0 V			1.3	V

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